



H2N5401

PNP EPITAXIAL PLANAR TRANSISTOR

Description

The H2N5401 is designed for general purpose applications requiring high breakdown voltages.

Features

- Complements to NPN Type H2N5551
- High Collector-Emitter Breakdown Voltage ($V_{CEO}=150V$ (@ $I_C=1mA$))

Absolute Maximum Ratings

- Maximum Temperatures
Storage Temperature $-55 \sim +150^{\circ}C$
Junction Temperature $+150^{\circ}C$ Maximum
- Maximum Power Dissipation
Total Power Dissipation ($T_a=25^{\circ}C$) 625 mW
- Maximum Voltages and Currents ($T_a=25^{\circ}C$)
VCBO Collector to Base Voltage $-160 V$
VCEO Collector to Emitter Voltage $-150 V$
VEBO Emitter to Base Voltage $-5 V$
IC Collector Current $-600 mA$

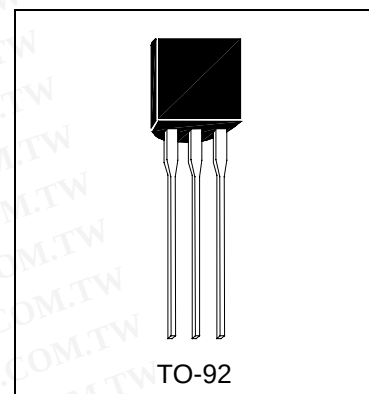
Characteristics ($T_a=25^{\circ}C$)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-160	-	-	V	$I_C=-100\mu A$, $I_E=0$
BVCEO	-150	-	-	V	$I_C=-1mA$, $I_B=0$
BVEBO	-5	-	-	V	$I_E=-10\mu A$, $I_C=0$
ICBO	-	-	-50	nA	$V_{CB}=-120V$, $I_E=0$
IEBO	-	-	-50	nA	$V_{EB}=-3V$, $I_C=0$
*VCE(sat)1	-	-	-0.2	V	$I_C=-10mA$, $I_B=-1mA$
*VCE(sat)2	-	-	-0.5	V	$I_C=-50mA$, $I_B=-5mA$
*VBE(sat)1	-	-	-1	V	$I_C=-10mA$, $I_B=-1mA$
*VBE(sat)2	-	-	-1	V	$I_C=-50mA$, $I_B=-5mA$
*hFE1	50	-	-		$V_{CE}=-5V$, $I_C=-1mA$
*hFE2	80	160	400		$V_{CE}=-5V$, $I_C=-10mA$
*hFE3	50	-	-		$V_{CE}=-5V$, $I_C=-50mA$
fT	100	-	300	MHz	$V_{CE}=-10V$, $I_C=-10mA$, $f=100MHz$
Cob	-	-	6	pF	$V_{CB}=-10V$, $f=1MHz$, $I_E=0$

*Pulse Test: Pulse Width $\leq 380\mu s$, Duty Cycle $\leq 2\%$

Classification of hFE2

Rank	A	N	C
Range	80-200	100-240	160-400

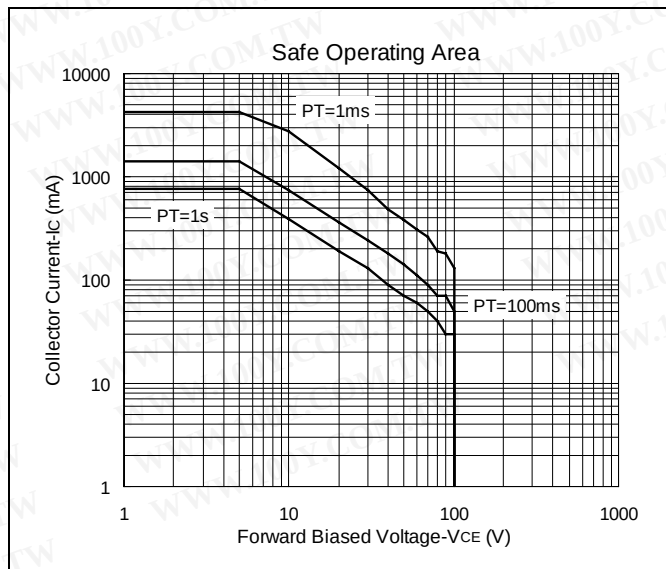
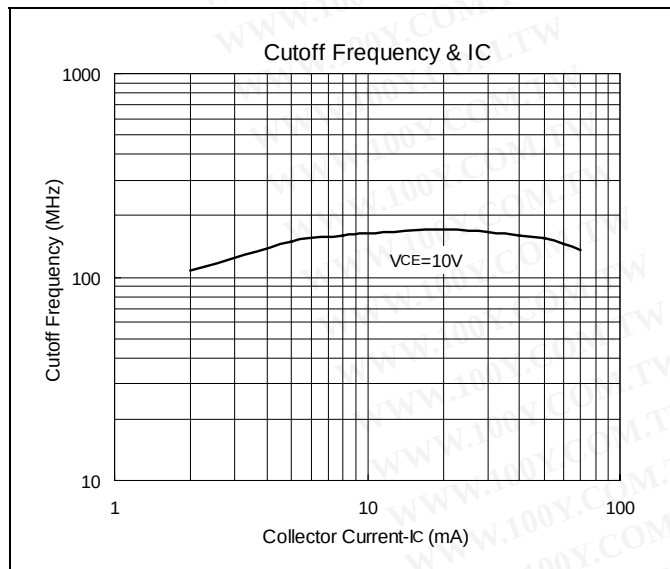
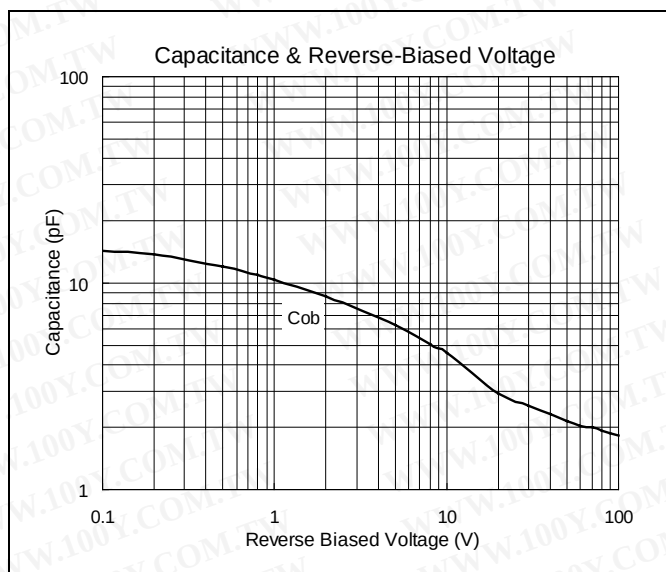
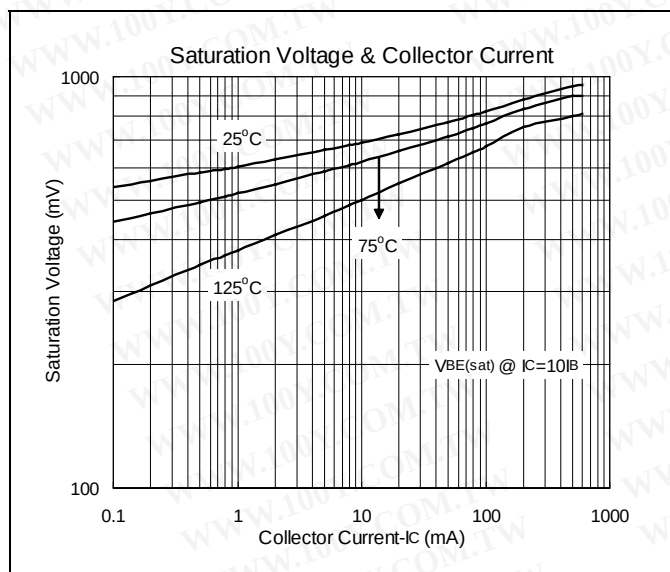
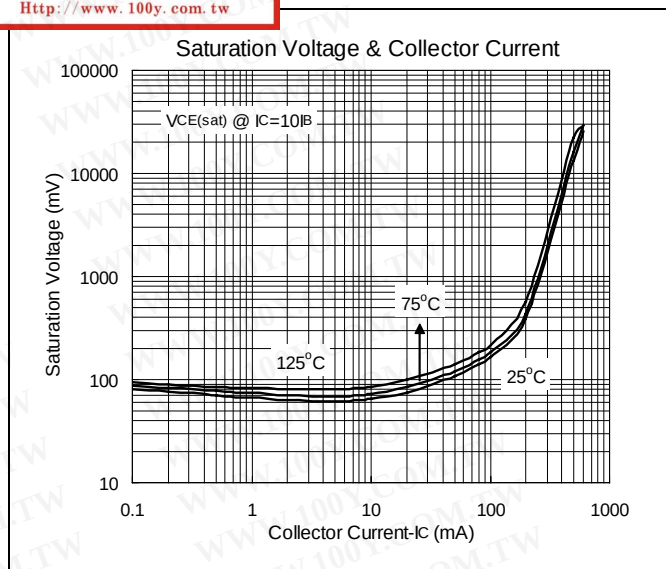
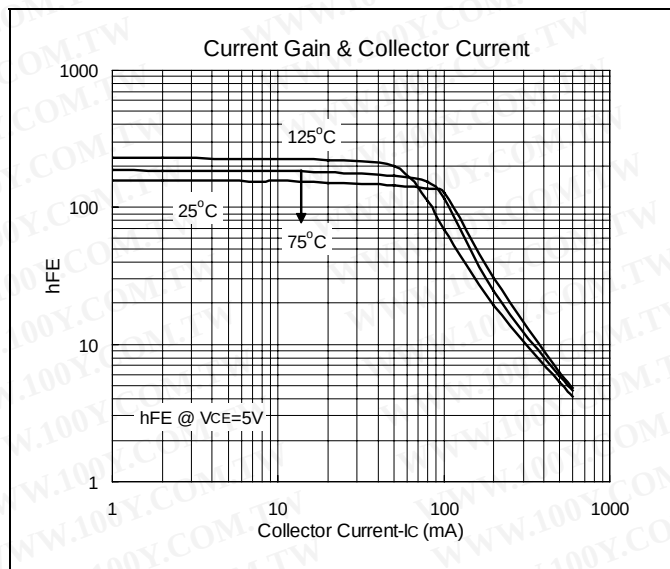


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Characteristics Curve

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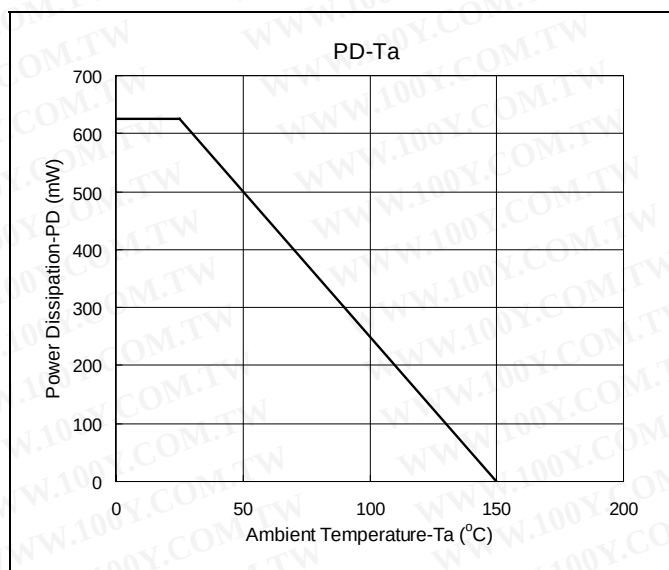




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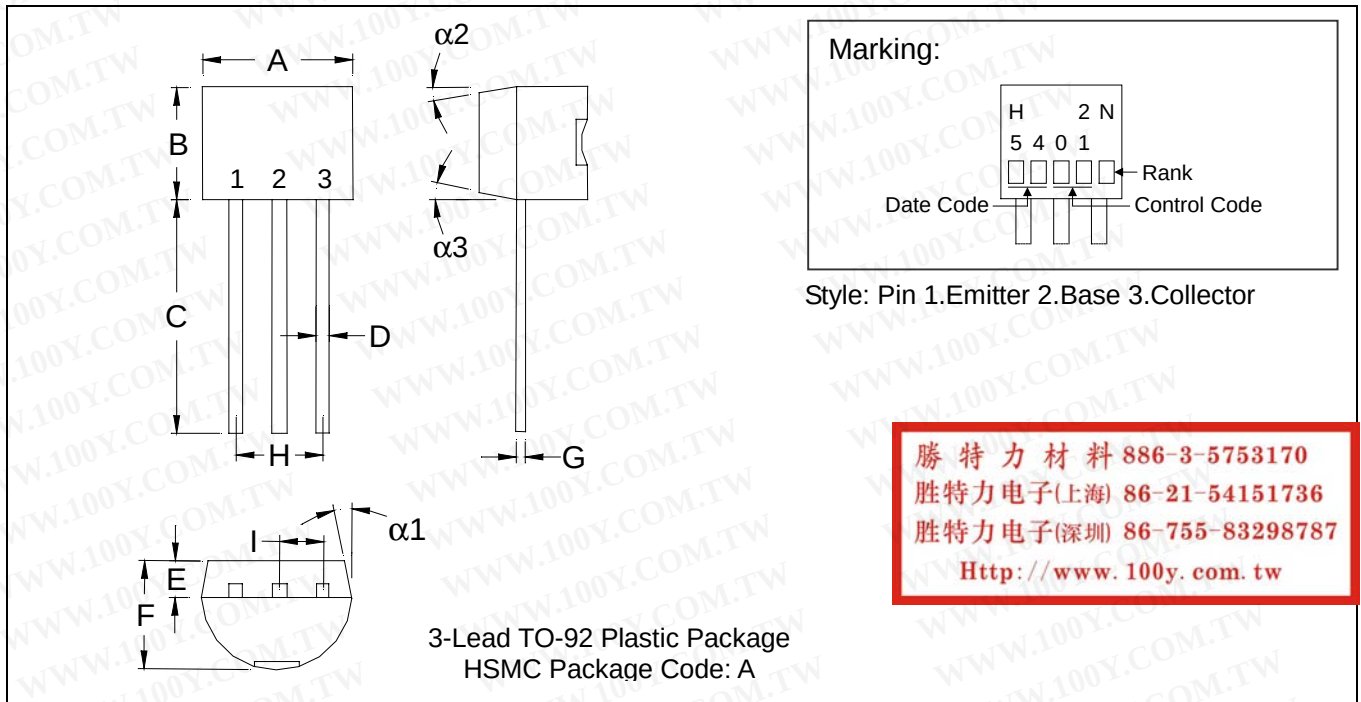
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TO-92 Dimension



*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1704	0.1902	4.33	4.83	G	0.0142	0.0220	0.36	0.56
B	0.1704	0.1902	4.33	4.83	H	-	*0.1000	-	*2.54
C	0.5000	-	12.70	-	I	-	*0.0500	-	*1.27
D	0.0142	0.0220	0.36	0.56	$\alpha 1$	-	*5°	-	*5°
E	-	*0.0500	-	*1.27	$\alpha 2$	-	*2°	-	*2°
F	0.1323	0.1480	3.36	3.76	$\alpha 3$	-	*2°	-	*2°

Notes: 1. Dimension and tolerance based on our Spec. dated Apr. 25, 1996.
2. Controlling dimension: millimeters.
3. Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
4. If there is any question with packing specification or packing method, please contact your local HSMC sales office.

Material:

- Lead: 42 Alloy; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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